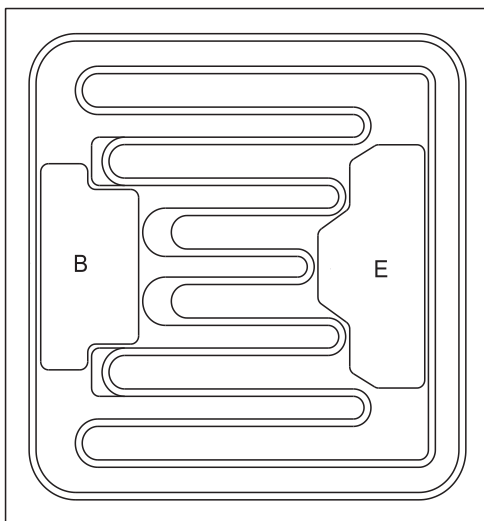


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31 x 31 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.9 x 11.8 MILS
Emitter Bonding Pad Area	6.5 x 13.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 15,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

11,300

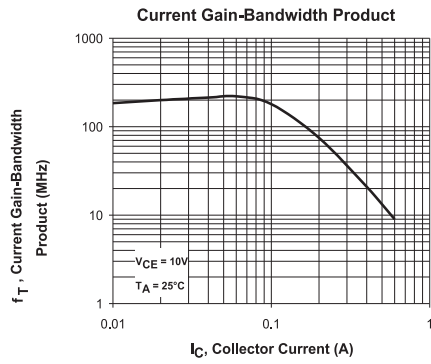
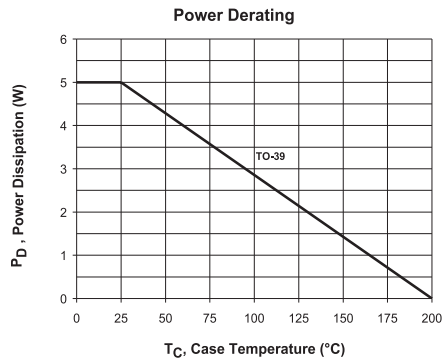
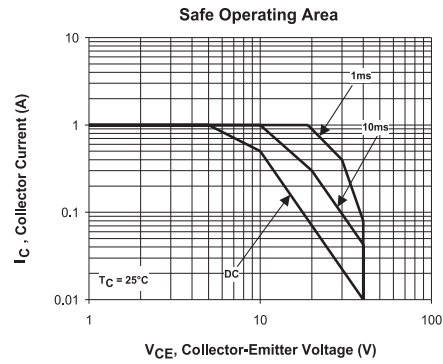
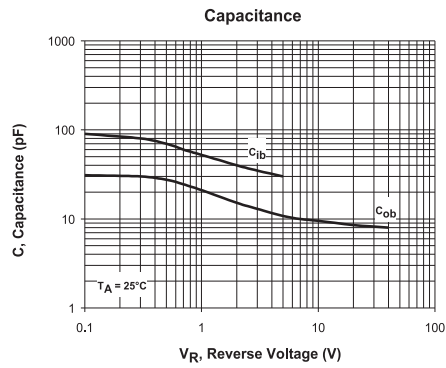
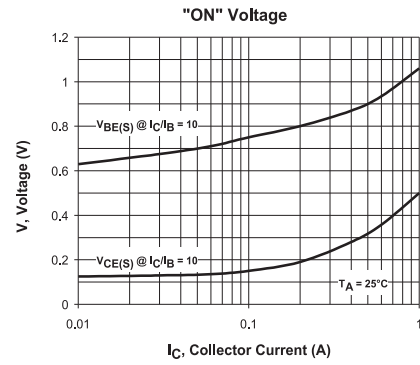
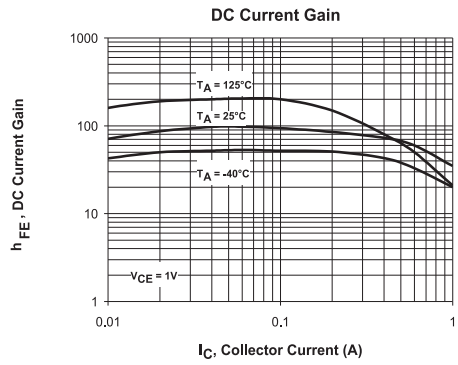
PRINCIPAL DEVICE TYPES

2N3467

2N3468

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